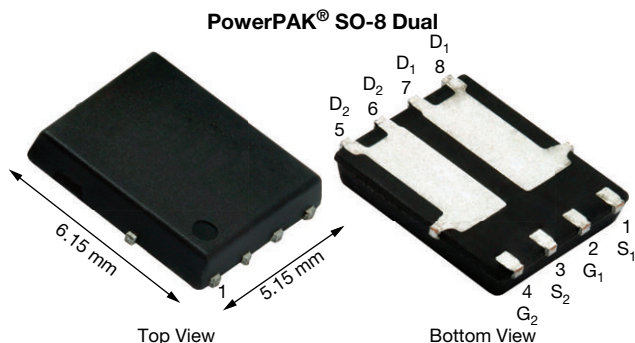


Dual N-Channel 30 V (D-S) MOSFET



FEATURES

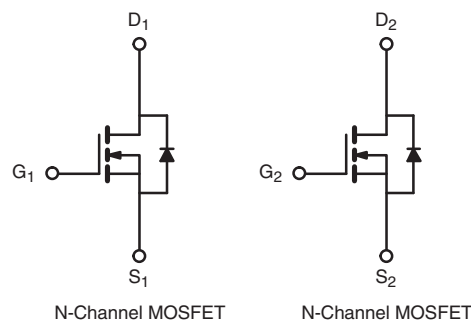
- TrenchFET® power MOSFET
- PWM optimized
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- System power DC/DC



| PRODUCT SUMMARY | | | |
|---------------------|----------------------------------|---------------------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) ^a | Q _g (TYP.) |
| 60 | 0.018 at V _{GS} = 10 V | 8 | 7.1 |
| | 0.021 at V _{GS} = 4.5 V | 8 | |

Ordering Information:

Si7972DP-T1-GE3 (lead (Pb)-free and halogen-free)

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | |
|---|------------------------|-----------------------------------|---------------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | V _{DS} | 60 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | |
| Continuous Drain Current (T _J = 150 °C) | T _C = 25 °C | I _D | 8 ^a | A |
| | T _C = 70 °C | | 8 ^a | |
| | T _A = 25 °C | | 8 ^a | |
| | T _A = 70 °C | | 8 ^a | |
| Pulsed Drain Current | | I _{DM} | 40 | A |
| Source-Drain Current Diode Current | T _C = 25 °C | I _S | 19 | |
| | T _A = 25 °C | | 3 ^{b, c} | |
| Maximum Power Dissipation | T _C = 25 °C | P _D | 22 | W |
| | T _C = 70 °C | | 14 | |
| | T _A = 25 °C | | 3.6 ^{b, c} | |
| | T _A = 70 °C | | 2.3 ^{b, c} | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +150 | °C |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|--------------|-------------------|------|------|------|
| PARAMETER | | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient ^{b, f} | t ≤ 10 s | R _{thJA} | 26 | 35 | °C/W |
| | Steady State | R _{thJC} | 4 | 5.5 | |

Notes

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.

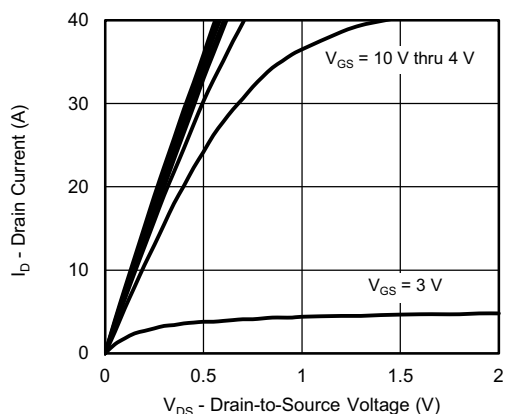
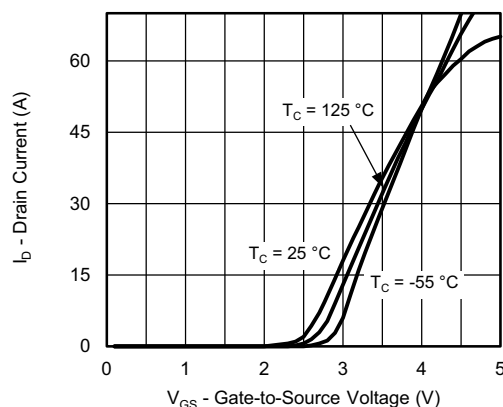
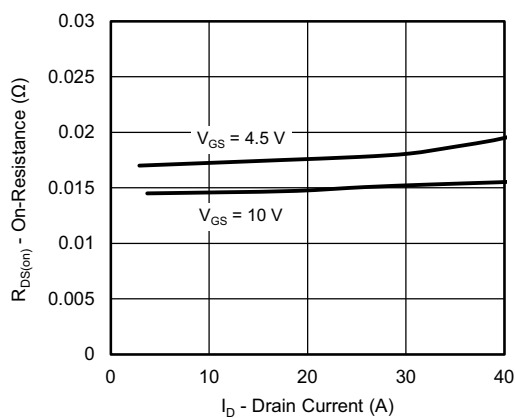
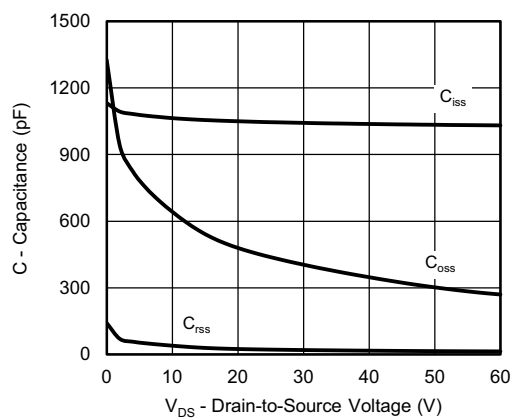
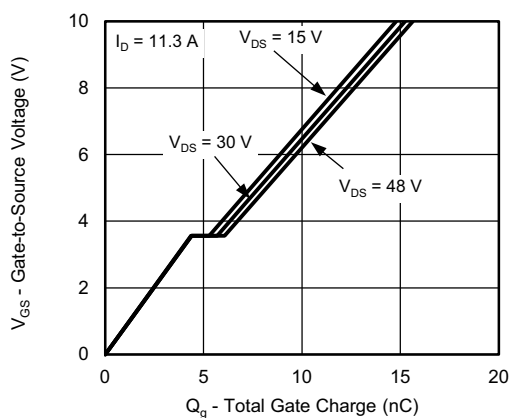
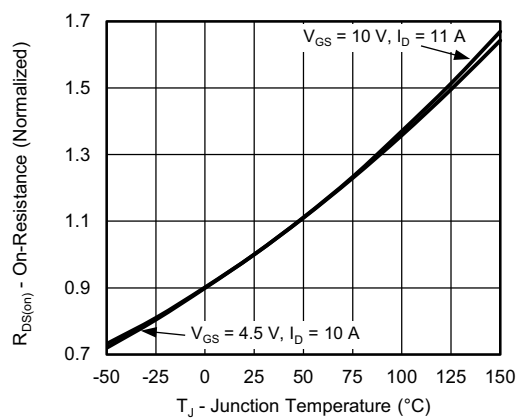


| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|---|--------------------------------------|---|------|-------|-------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 60 | - | - | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = 250 μA | - | 38 | - | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | I _D = 250 μA | - | -4.9 | - | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 1.2 | - | 2.7 | V |
| Gate-Body Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | - | - | 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V | - | - | 1 | μA |
| | | V _{DS} = 60 V, V _{GS} = 0 V, T _J = 85 °C | - | - | 10 | |
| On-State Drain Current ^b | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 10 V | 60 | - | - | A |
| Drain-Source On-State Resistance ^b | R _{DS(on)} | V _{GS} = 10 V, I _D = 11 A | - | 0.015 | 0.018 | Ω |
| | | V _{GS} = 4.5 V, I _D = 10 A | - | 0.017 | 0.021 | |
| Forward Transconductance ^b | g _{fs} | V _{DS} = 30 V, I _D = 11 A | - | 38 | - | S |
| Dynamic ^a | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz | - | 1050 | - | pF |
| Output Capacitance | C _{oss} | | - | 435 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 20 | - | |
| Total Gate Charge | Q _g | V _{DS} = 30 V, V _{GS} = 10 V, I _D = 11 A | - | 15.2 | 23 | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} = 30 V, V _{GS} = 4.5 V, I _D = 11 A | - | 7.1 | 11 | |
| Gate-Drain Charge | Q _{gd} | | - | 4.4 | - | |
| | | | - | 1.3 | - | |
| Gate Resistance | R _g | f = 1 MHz | 0.12 | 0.6 | 1.2 | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 30 V, R _L = 3.45 Ω I _D ≅ 8.7 A, V _{GEN} = 4.5 V, R _g = 1 Ω | - | 15 | 120 | ns |
| Rise Time | t _r | | - | 80 | 30 | |
| Turn-Off Delay Time | t _{d(off)} | | - | 15 | 30 | |
| Fall Time | t _f | | - | 15 | 30 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 30 V, R _L = 3.45 Ω I _D ≅ 8.7 A, V _{GEN} = 10 V, R _g = 1 Ω | - | 10 | 15 | |
| Rise Time | t _r | | - | 25 | 40 | |
| Turn-Off Delay Time | t _{d(off)} | | - | 20 | 30 | |
| Fall Time | t _f | | - | 10 | 15 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | - | - | 8 | A |
| Pulse Diode Forward Current ^a | I _{SM} | | - | - | 40 | |
| Body Diode Voltage | V _{SD} | I _S = 8.7 A | - | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 8.7 A, dI/dt = 100 A/μs, T _J = 25 °C | - | 34 | 51 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | - | 30 | 45 | nC |
| Reverse Recovery Fall Time | t _a | | - | 16 | - | ns |
| Reverse Recovery Rise Time | t _b | | - | 18 | - | |

Notes

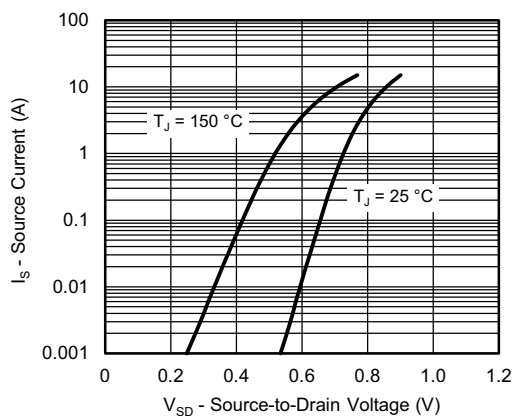
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

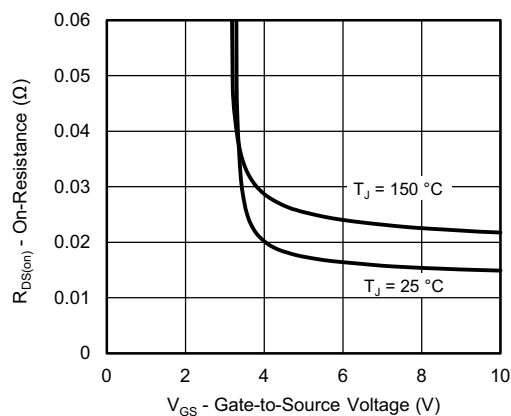
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature



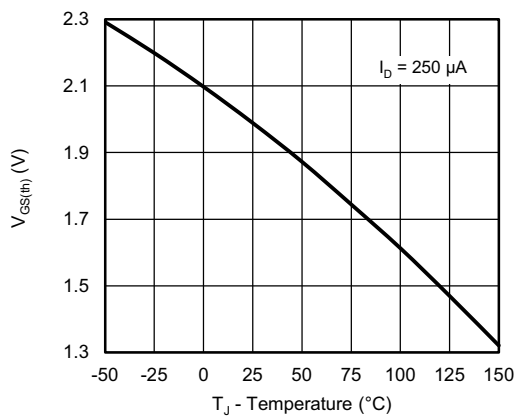
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



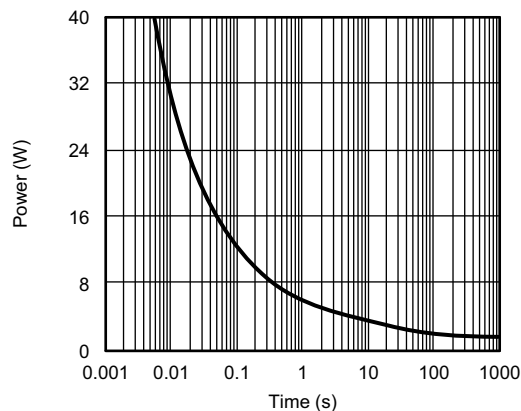
Source-Drain Diode Forward Voltage



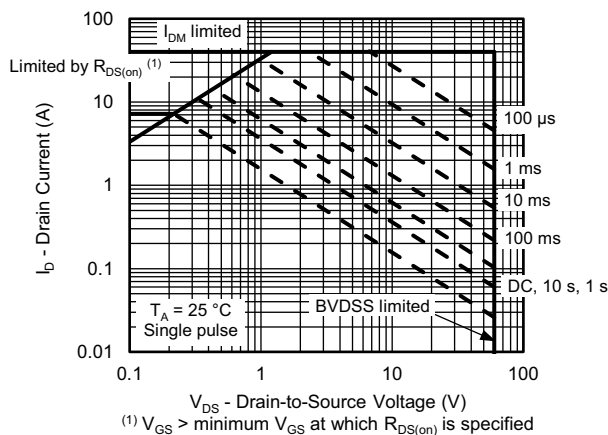
On-Resistance vs. Gate-to-Source Voltage



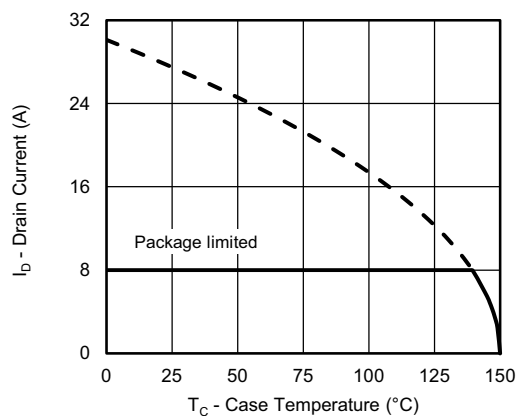
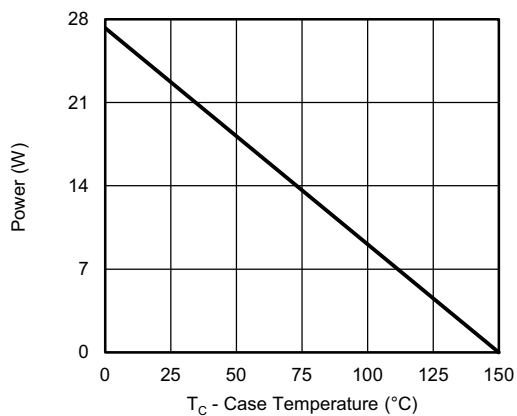
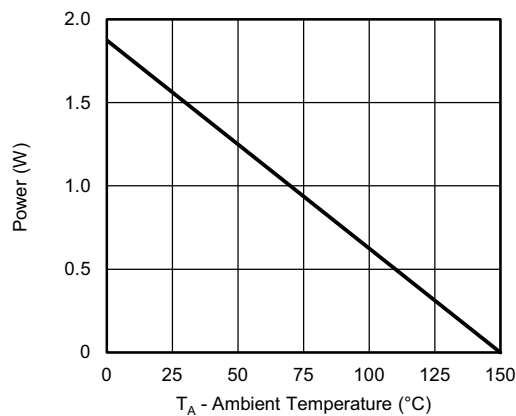
Threshold Voltage



Single Pulse Power



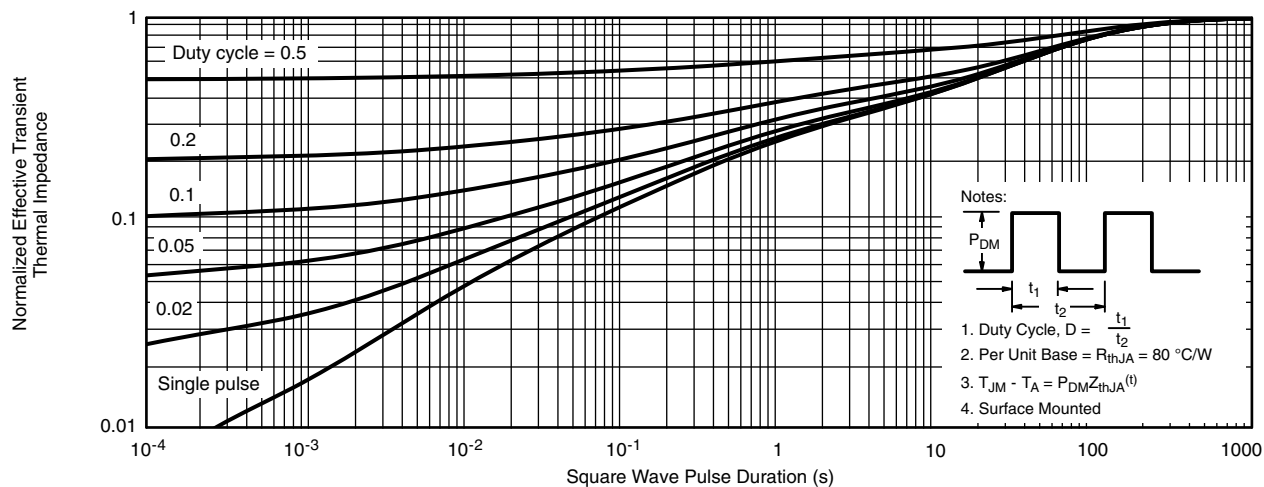
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case

Power, Junction-to-Ambient
Note

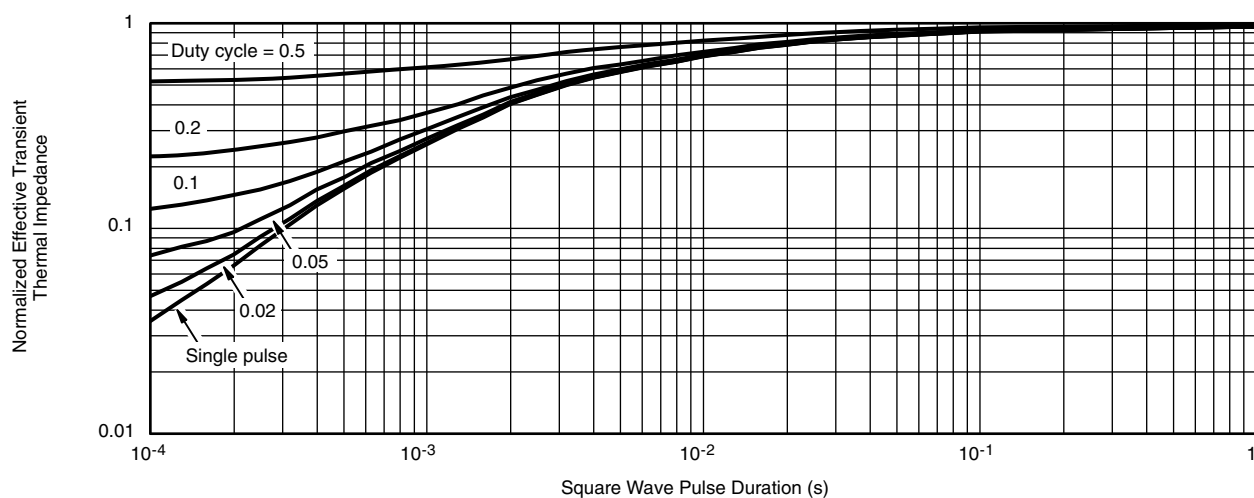
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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